

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology
- ★ 100% EAS Guaranteed

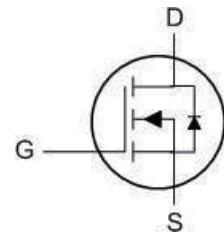
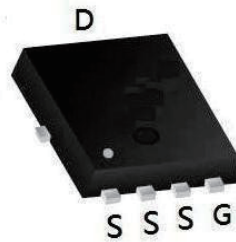
**Product Summary**

BVDSS	RDS(on)	ID
20V	6.3mΩ	40A

**Description**

The 40N02D is the high cell density trenched N-ch MOSFETs, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications.

The 40N02D meet the RoHS and Green Product, requirement 100% EAS guaranteed with full function reliability approved.

**PRPAK3\*3 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	40	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	23	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	210	A
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>3</sup>	36	mJ
I <sub>AS</sub>	Avalanche Current	21	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	15	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	4.8	°C/W

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$  unless otherwise specified)**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.7	1.1	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <sup>note3</sup>	$V_{GS}=4.5V, I_D=25A$	-	6.3	8	m $\Omega$
		$V_{GS}=2.5V, I_D=10A$	-	8.8	13	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, f=1.0MHz$	-	1458	-	pF
$C_{oss}$	Output Capacitance		-	238	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	212	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=10V, I_D=25A, V_{GS}=4.5V$	-	19	-	nC
$Q_{gs}$	Gate-Source Charge		-	3	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	6.4	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V, I_D=10A, R_{GEN}=3\Omega,$ $V_{GS}=4.5V$	-	10	-	ns
$t_r$	Turn-on Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	39	-	ns
$t_f$	Turn-off Fall Time		-	19	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=20A, dI/dt=100A/\mu s$	-	25	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	20	-	nC

**Notes:**

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition:  $T_J=25^\circ\text{C}, V_{DD}=10V, V_G=4.5V, R_G=25\Omega, L=0.5mH, I_{AS}=12A$
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

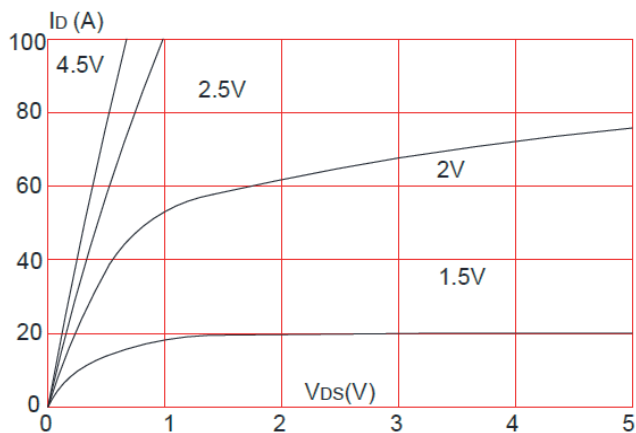


Figure 2: Typical Transfer Characteristics

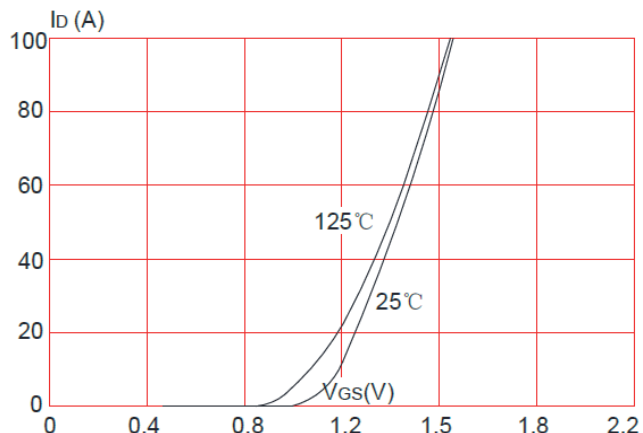


Figure 3: On-resistance vs. Drain Current

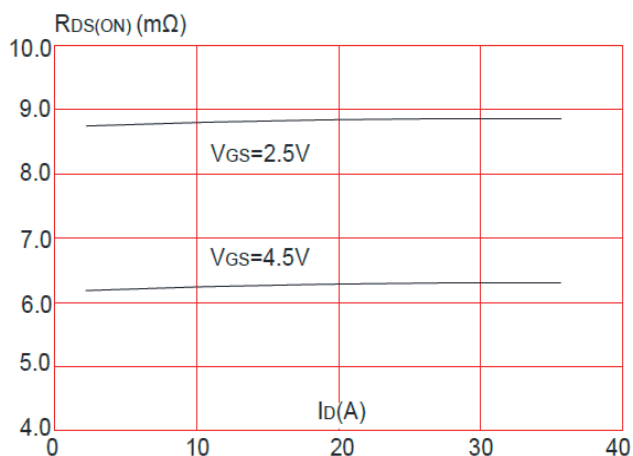


Figure 4: Body Diode Characteristics

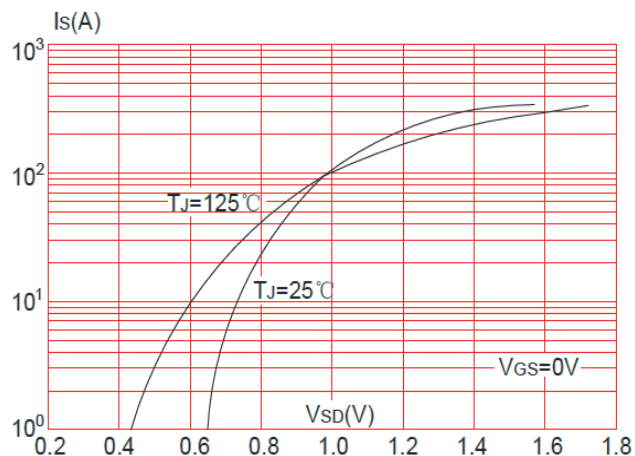


Figure 5: Gate Charge Characteristics

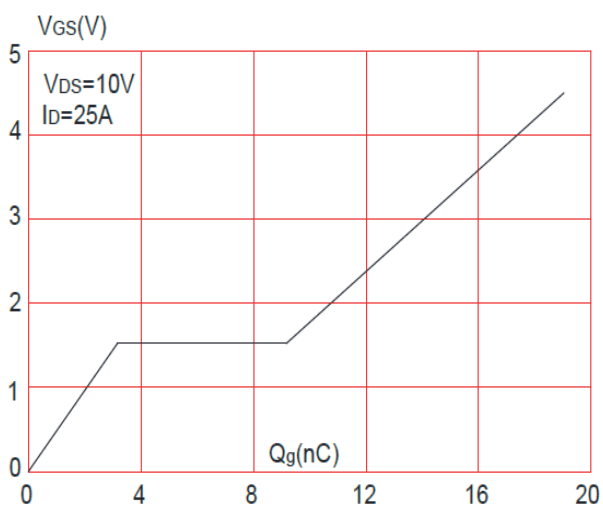
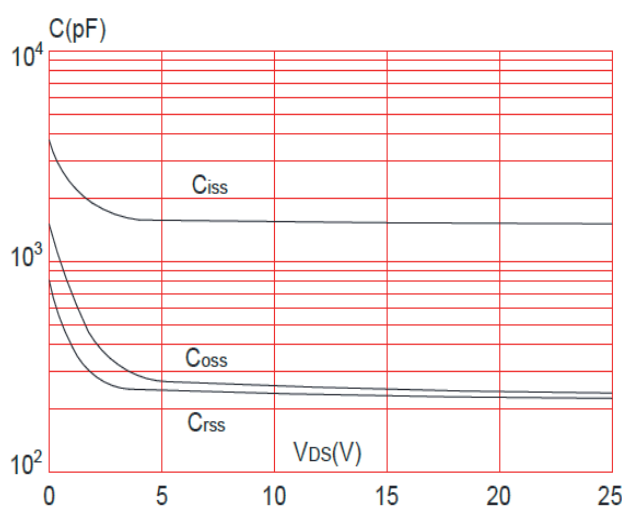


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage

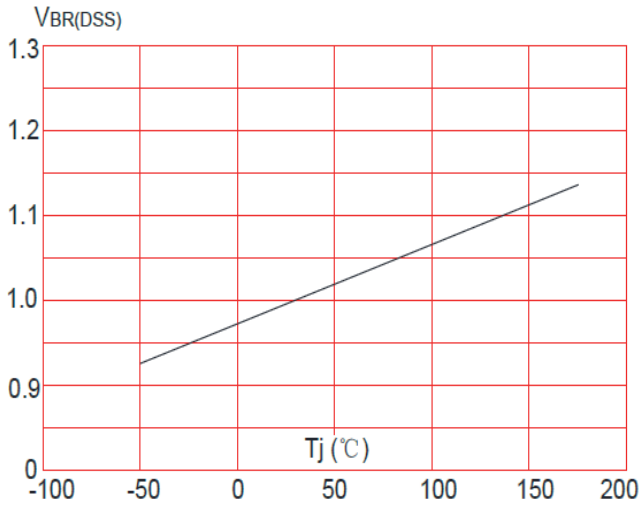


Figure 8: Normalized on Resistance vs. Junction Temperature

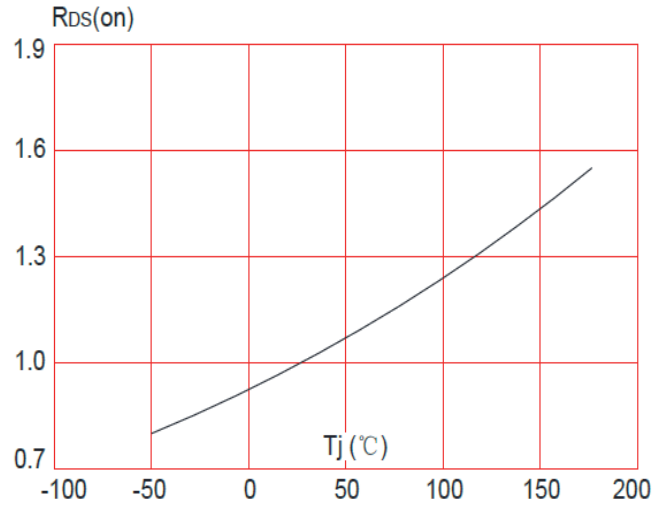


Figure 9: Maximum Safe Operating Area

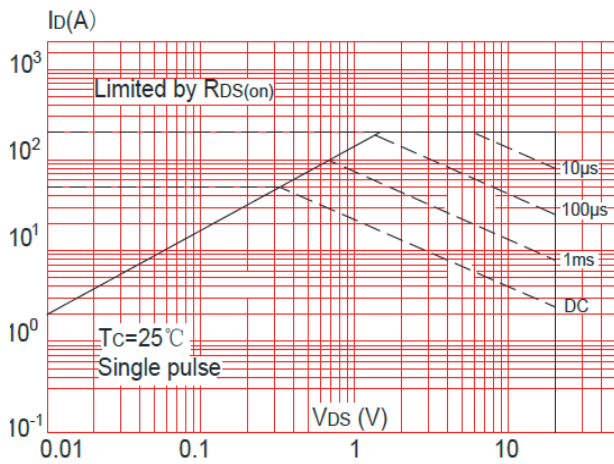


Figure 10: Maximum Continuous Drain Current vs. Temperature

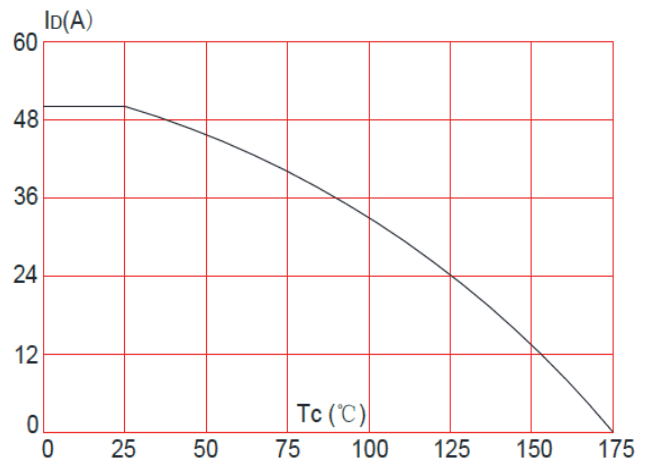
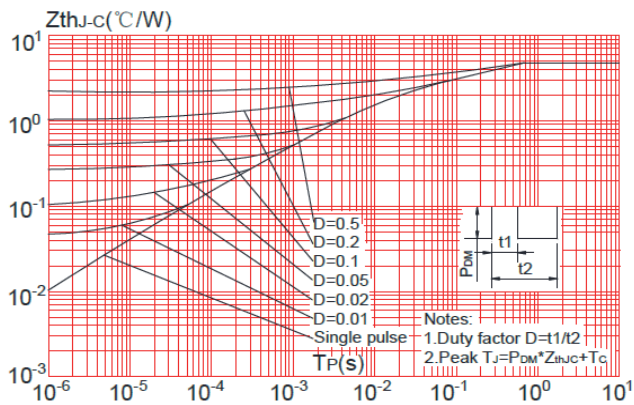
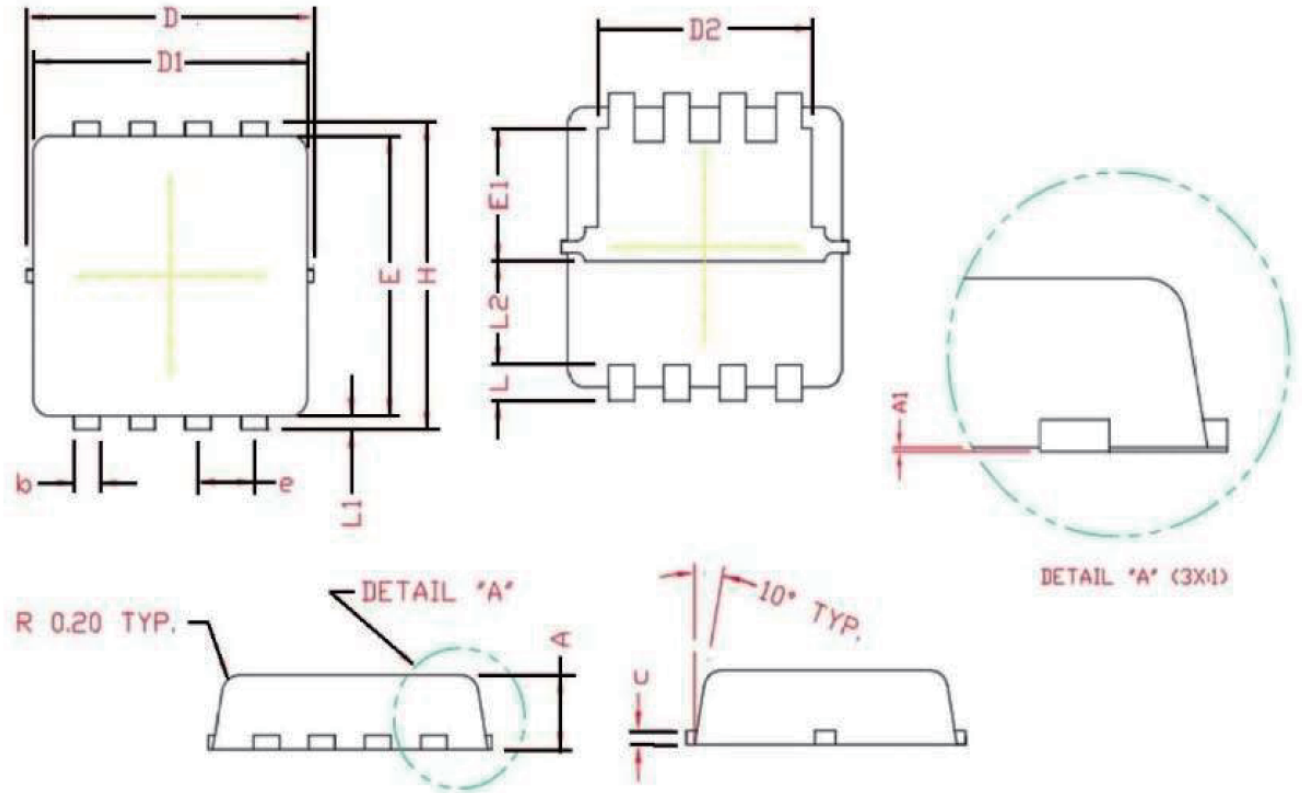


Figure 11: Maximum Effective Transient Thermal Impedance



PDFN3\*3-8L Package Information



Symbol	MILLMETER		
	MIN	MON	MAX
A	0.70	0.80	0.90
A1	0.00	0.03	0.05
b	0.24	0.30	0.35
c	0.10	0.15	0.20
D	3.25	3.32	3.40
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.00	3.10	3.20
E1	1.35	1.45	1.55
e	0.65BSC.		
H	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.10	0.15	0.20
L2	1.13REF.		

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